



STGW20NC60VD

N-CHANNEL 30A - 600V TO-247

Very Fast PowerMESH™ IGBT

Table 1: General Features

TYPE	V _{CES}	V _{CE(sat)} (Max) @25°C	I _C @100°C
STGW20NC60VD	600 V	< 2.5 V	30 A

- OFF LOSSES INCLUDE TAIL CURRENT
- LOSSES INCLUDE DIODE RECOVERY ENERGY
- HIGH CURRENT CAPABILITY
- HIGH FREQUENCY OPERATION UP TO 50 KHz
- VERY SOFT ULTRA FAST RECOVERY ANTIPARALLEL DIODE
- LOWER C_{RES} /C_{IES} RATIO
- NEW GENERATION PRODUCTS WITH TIGHTER PARAMETER DISTRIBUTION

DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "V" identifies a family optimized for high frequency applications.

APPLICATIONS

- HIGH FREQUENCY INVERTERS
- SMPS and PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES
- UPS
- MOTOR DRIVERS

Figure 1: Package

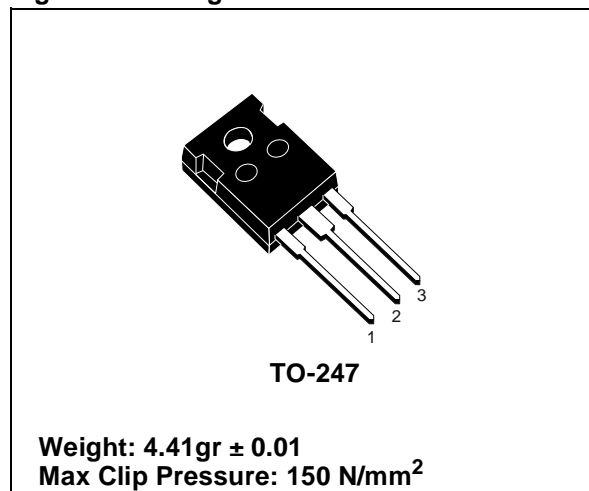


Figure 2: Internal Schematic Diagram

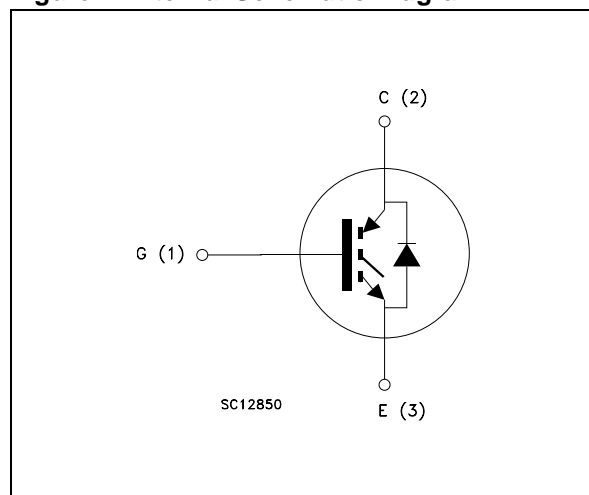


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGW20NC60VD	GW20NC60VD	TO-247	TUBE

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value	Symbol
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600	V
V _{ECR}	Reverse Battery Protection	20	V
V _{GE}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current (continuous) at 25°C (#)	60	A
I _C	Collector Current (continuous) at 100°C (#)	30	A
I _{CM} (1)	Collector Current (pulsed)	100	A
I _f	Diode RMS Forward Current at T _C = 25°C	30	A
P _{TOT}	Total Dissipation at T _C = 25°C	200	W
	Derating Factor	1.6	W/°C
T _{stg}	Storage Temperature	– 55 to 150	°C
T _j	Operating Junction Temperature		

(1)Pulse width limited by max. junction temperature.

Table 4: Thermal Data

		Min.	Typ.	Max.	
R _{thj-case}	Thermal Resistance Junction-case (IGBT)	--	--	0.625	°C/W
R _{thj-case}	Thermal Resistance Junction-case (Diode)	--	--	1.5	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient	--	--	50	°C/W
T _L	Maximum Lead Temperature for Soldering Purpose (1.6 mm from case, for 10 sec.)		300		°C

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)**Table 5: Off**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collectro-Emitter Breakdown Voltage	I _C = 1 mA, V _{GE} = 0	600			V
I _{CES}	Collector-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = Max Rating T _C =25°C T _C =125°C			10 1	μA mA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ± 20 V , V _{CE} = 0			± 100	nA

Table 6: On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250 μA	3.75		5.75	V
V _{CE(SAT)}	Collector-Emitter Saturation Voltage	V _{GE} = 15 V, I _C = 20A, T _j = 25°C V _{GE} = 15 V, I _C = 20A, T _j = 125°C		1.8 1.7	2.5	V V

(#)
(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

ELECTRICAL CHARACTERISTICS (CONTINUED)**Table 7: Dynamic**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}(1)$	Forward Transconductance	$V_{CE} = 15\text{ V}$, $I_C = 20\text{ A}$		15		S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$		2200 225 50		pF pF pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 390\text{ V}$, $I_C = 20\text{ A}$, $V_{GE} = 15\text{ V}$, (see Figure 21)		100 16 45	140	nC nC nC
I_{CL}	Turn-Off SOA Minimum Current	$V_{clamp} = 480\text{ V}$, $T_J = 150^\circ\text{C}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$	100			A

Table 8: Switching On

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $(di/dt)_{on}$ $E_{on}(2)$	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 390\text{ V}$, $I_C = 20\text{ A}$ $R_G = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 25^\circ\text{C}$ (see Figure 19)		31 11 1600 220	300	ns ns A/ μs μJ
$t_{d(on)}$ t_r $(di/dt)_{on}$ $E_{on}(2)$	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 390\text{ V}$, $I_C = 20\text{ A}$ $R_G = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125^\circ\text{C}$ (see Figure 19)		31 11.5 1500 450		ns ns A/ μs μJ

2) E_{on} is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs & DIODE are at the same temperature (25°C and 125°C)

Table 9: Switching Off

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off}(3)$ E_{ts}	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 390\text{ V}$, $I_C = 20\text{ A}$, $R_{GE} = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$ $T_J = 25^\circ\text{C}$ (see Figure 19)		28 100 75 330 550	450 750	ns ns ns μJ μJ
$t_r(V_{off})$ $t_{d(off)}$ t_f $E_{off}(3)$ E_{ts}	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 390\text{ V}$, $I_C = 20\text{ A}$, $R_{GE} = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$ $T_J = 125^\circ\text{C}$ (see Figure 19)		66 150 130 770 1220		ns ns ns μJ μJ

(3) Turn-off losses include also the tail of the collector current.

Table 10: Collector-Emitter Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_f	Forward On-Voltage	$I_f = 10\text{ A}$ $I_f = 10\text{ A}, T_j = 125\text{ °C}$		1.3 1	2.0	V V
t_{rr} t_a Q_{rr} I_{rrm} S	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current Softness factor of the diode	$I_f = 20\text{ A}, V_R = 40\text{ V},$ $T_j = 25\text{ °C}, di/dt = 100\text{ A/}\mu\text{s}$ (see Figure 22)		44 32 66 3 0.375		ns ns nC A
t_{rr} t_a Q_{rr} I_{rrm} S	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current Softness factor of the diode	$I_f = 20\text{ A}, V_R = 40\text{ V},$ $T_j = 125\text{ °C}, di/dt = 100\text{ A/}\mu\text{s}$ (see Figure 22)		88 56 237 5.4 0.57		ns ns nC A

Figure 3: Output Characteristics

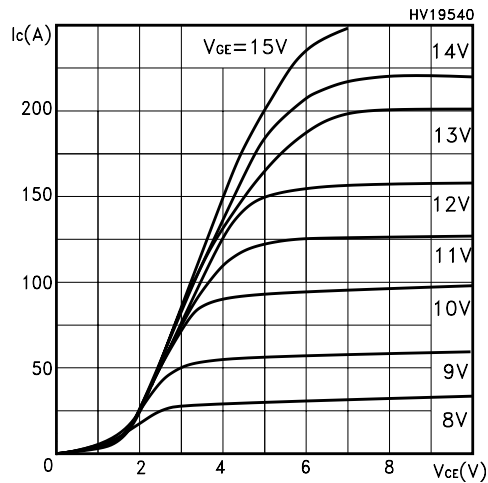


Figure 4: Transconductance

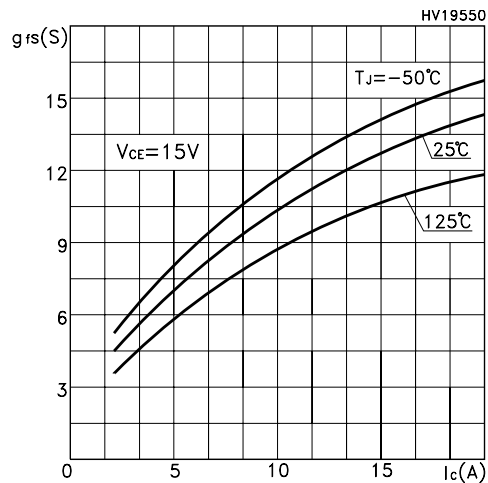


Figure 5: Collector-Emitter On Voltage vs Collector Current

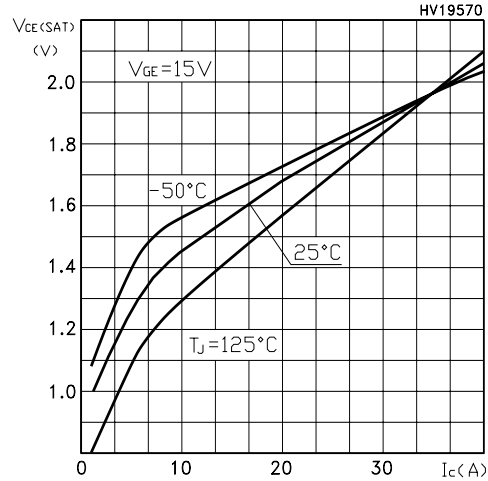


Figure 6: Transfer Characteristics

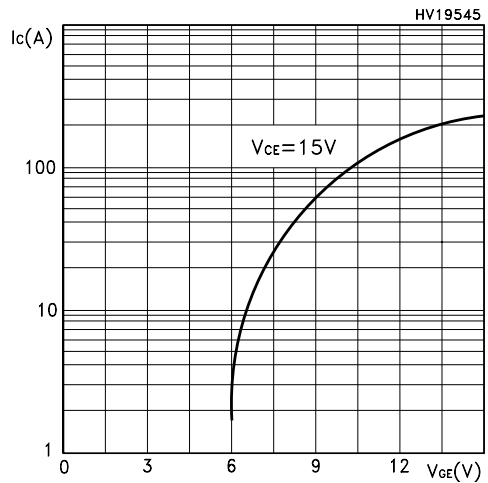


Figure 7: Collector-Emitter On Voltage vs Temperature

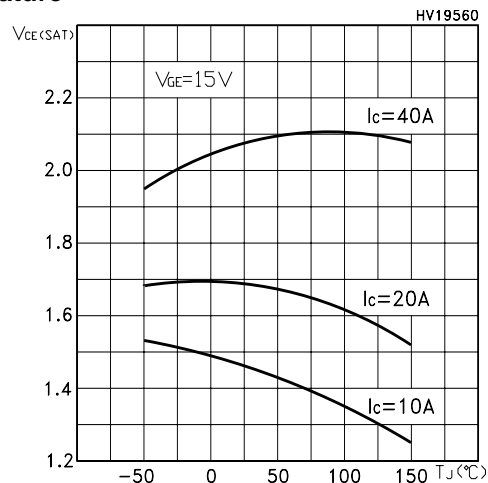


Figure 8: Normalized Gate Threshold vs Temperature

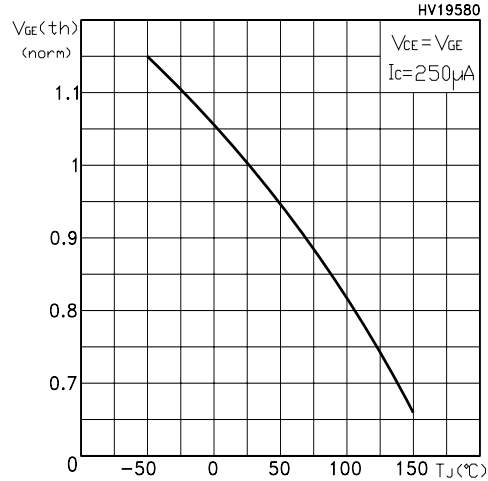


Figure 9: Normalized Breakdown Voltage vs Temperature

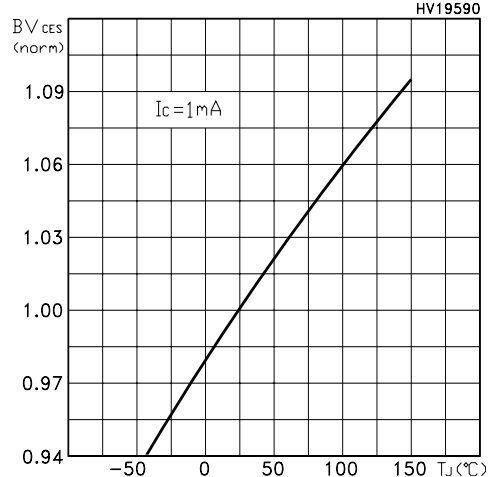


Figure 10: Capacitance Variations

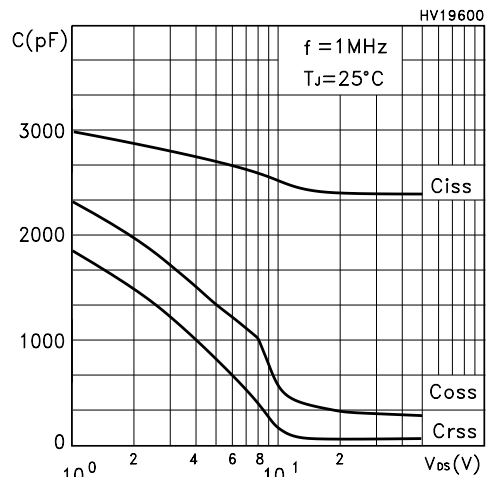


Figure 11: Total Switching Losses vs Gate Resistance

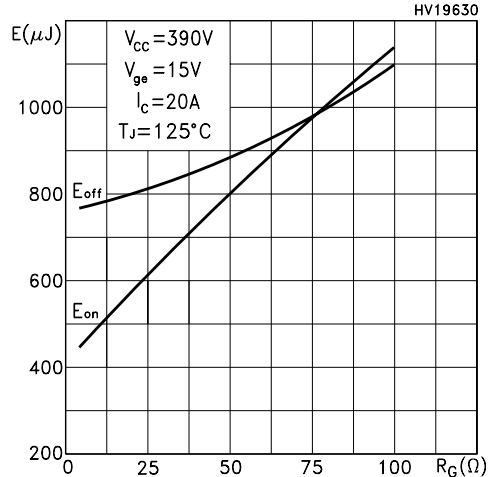


Figure 12: Gate Charge vs Gate-Emitter Voltage

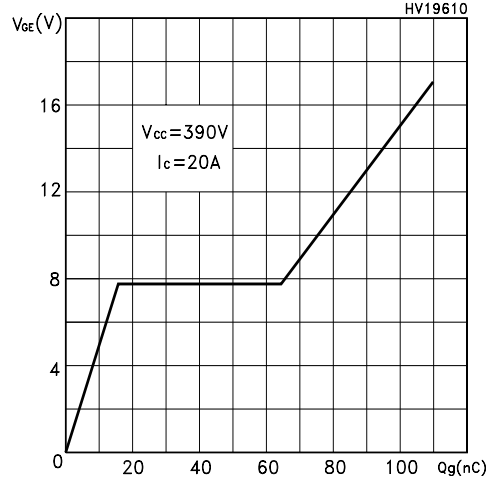


Figure 13: Total Switching Losses vs Temperature

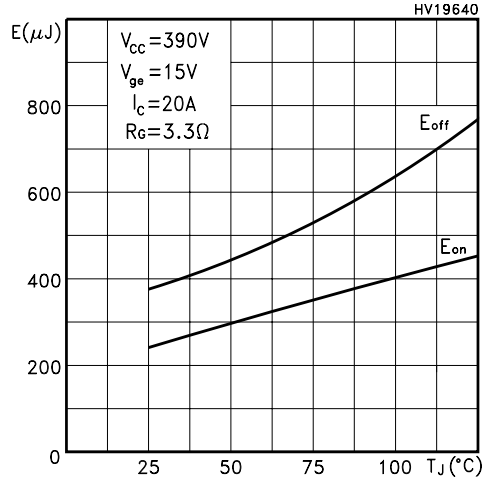


Figure 14: Total Switching Losses vs Collector Current

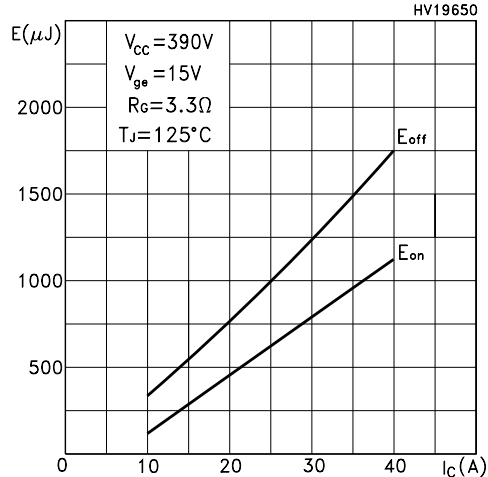


Figure 15: Thermal Impedance

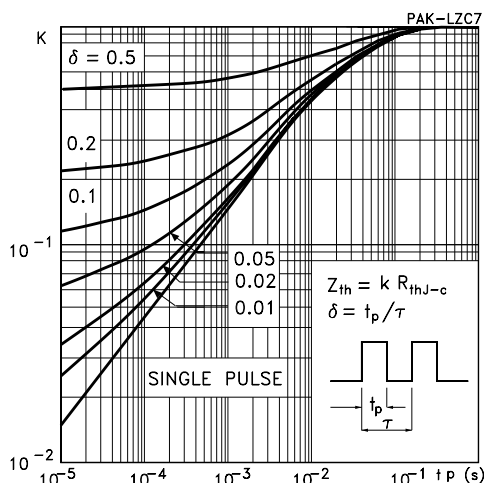


Figure 16: Turn-Off SOA

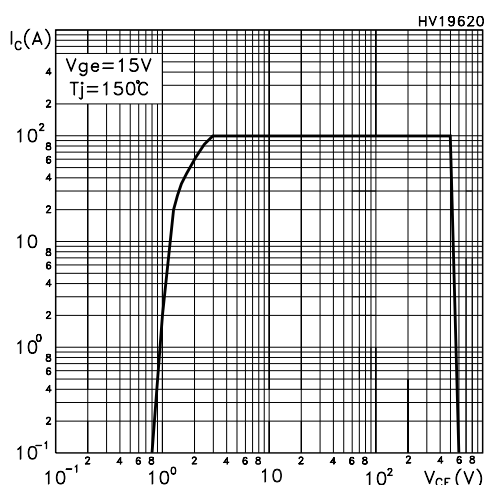


Figure 17: Emitter-Collector Diode Characteristics

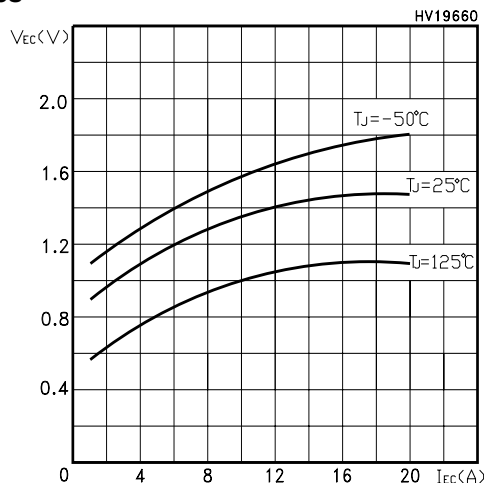
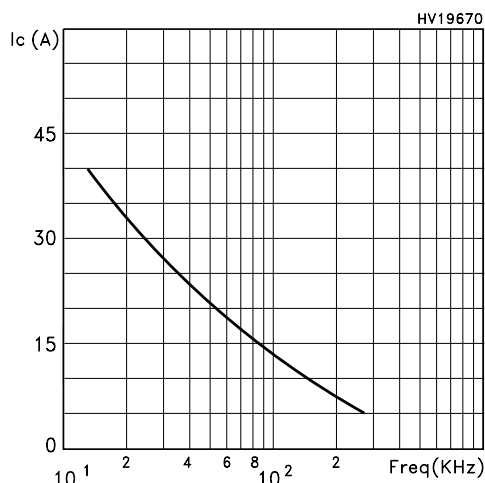


Figure 18: Ic vs Frequency



For a fast IGBT suitable for high frequency applications, the typical collector current vs. maximum operating frequency curve is reported. That frequency is defined as follows:

$$f_{MAX} = (P_D - P_C) / (E_{ON} + E_{OFF})$$

1) The maximum power dissipation is limited by maximum junction to case thermal resistance:

$$P_D = \Delta T / R_{THJ-C}$$

considering $\Delta T = T_J - T_C = 125^\circ\text{C} - 75^\circ\text{C} = 50^\circ\text{C}$

2) The conduction losses are:

$$P_C = I_C * V_{CE(SAT)} * \delta$$

with 50% of duty cycle, V_{CESAT} typical value @ 125°C .

3) Power dissipation during ON & OFF commutations is due to the switching frequency:

$$P_{SW} = (E_{ON} + E_{OFF}) * \text{freq.}$$

4) Typical values @ 125°C for switching losses are used (test conditions: $V_{CE} = 390\text{V}$, $V_{GE} = 15\text{V}$, $R_G = 3.3\text{ Ohm}$). Furthermore, diode recovery energy is included in the E_{ON} (see note 2), while the tail of the collector current is included in the E_{OFF} measurements (see note 3).

Figure 19: Test Circuit for Inductive Load Switching

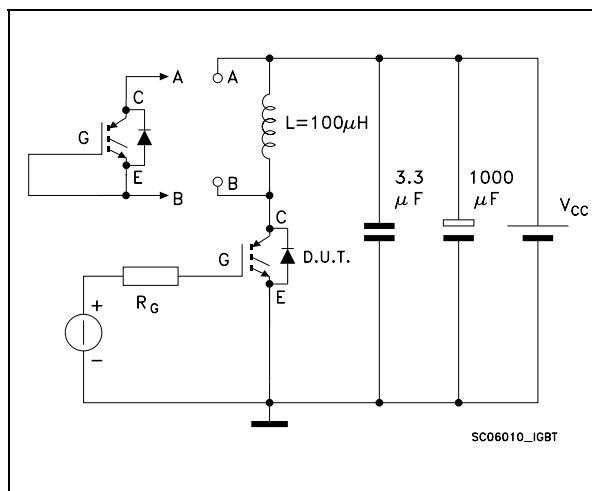


Figure 20: Switching Waveforms

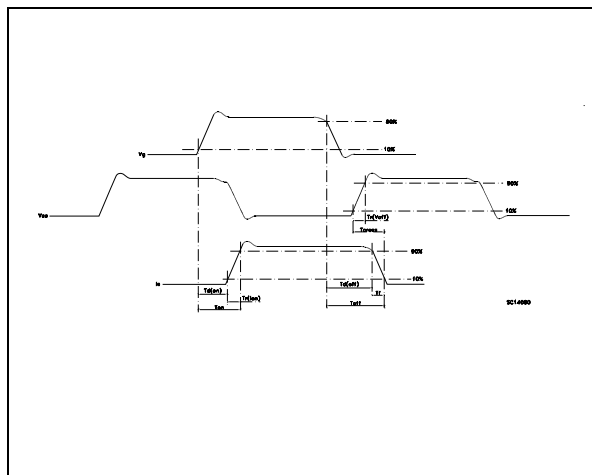


Figure 21: Gate Charge Test Circuit

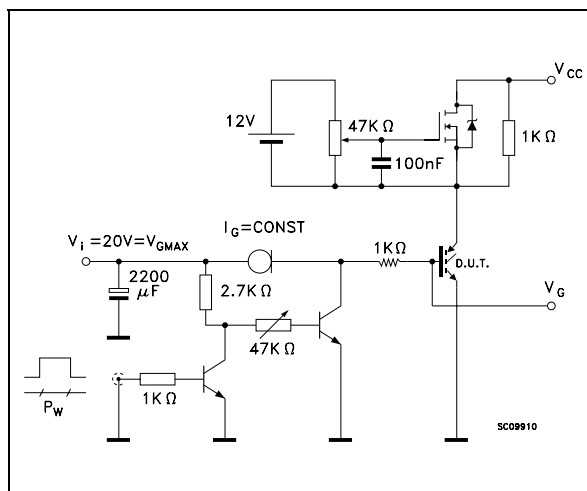


Figure 22: Diode Recovery Times Waveform

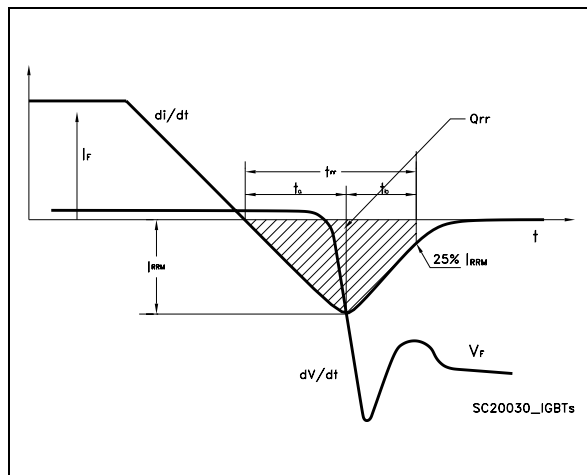
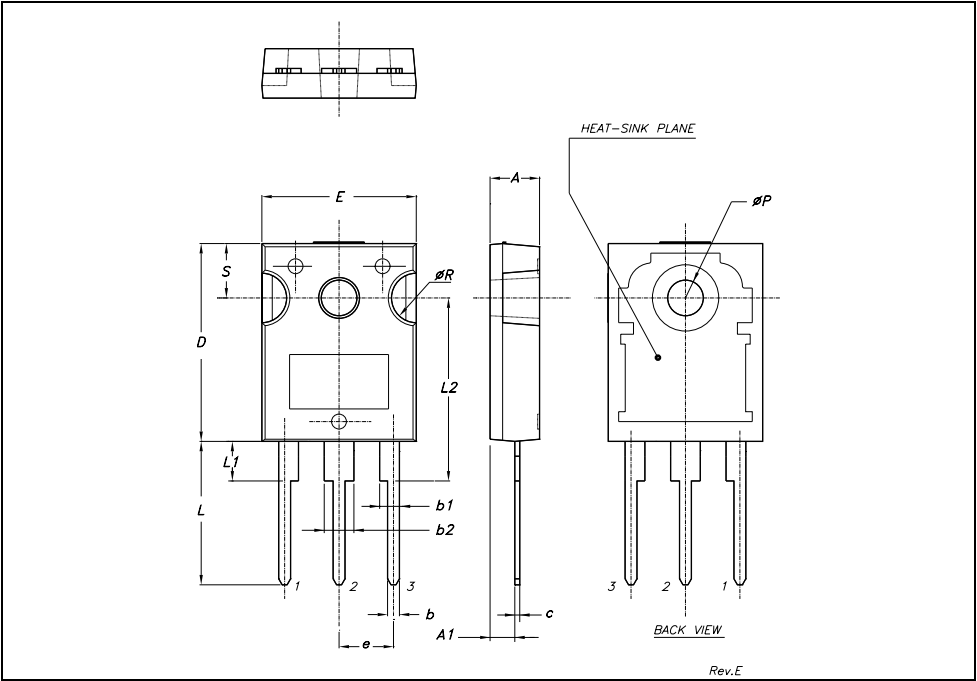


Table 11: Revision History

Date	Revision	Description of Changes
12-July-2004	4	Stylesheet update. Added Max Values see Table 8 and 9 Added Figure 22

TO-247 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.85		5.15	0.19		0.20
A1	2.20		2.60	0.086		0.102
b	1.0		1.40	0.039		0.055
b1	2.0		2.40	0.079		0.094
b2	3.0		3.40	0.118		0.134
c	0.40		0.80	0.015		0.03
D	19.85		20.15	0.781		0.793
E	15.45		15.75	0.608		0.620
e		5.45			0.214	
L	14.20		14.80	0.560		0.582
L1	3.70		4.30	0.14		0.17
L2		18.50			0.728	
øP	3.55		3.65	0.140		0.143
øR	4.50		5.50	0.177		0.216
S		5.50			0.216	



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